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IRFF330

3.5A, 400V, 1.000 Ohm, N-Channel Power MOSFET

This N-Channel enhancement mode silicon gate power field effect transistor is an advanced power MOSFET designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Features

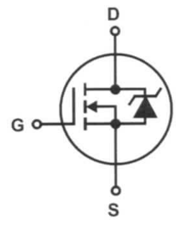
- 3.5A, 400V
- $r_{DS(ON)} = 1.000\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance

Ordering Information

PART NUMBER	PACKAGE	BRAND
IRFF330	TO-205AF	IRFF330

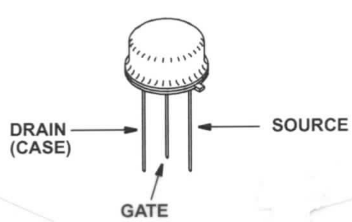
NOTE: When ordering, include the entire part number.

Symbol



Packaging

JEDEC TO-205AF



Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specified

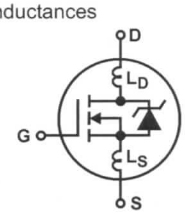
		IRFF330	UNITS
Drain to Source Voltage (Note 1)	V_{DS}	400	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR}	400	V
Continuous Drain Current	I_D	3.5	A
Pulsed Drain Current (Note 3)	I_{DM}	14	A
Gate to Source Voltage	V_{GS}	±20	V
Maximum Power Dissipation	P_D	25	W
Linear Derating Factor		0.2	W/^{o}C
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS}	300	mJ
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	^{o}C
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	^{o}C
Package Body for 10s, See Techbrief 334	T_{pkg}	260	^{o}C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

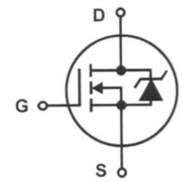
NOTE:

1. $T_J = 25^oC$ to 125^oC.

Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$ (Figure 10)	400	-	-	V
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	2.0	-	4.0	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = Rated BV_{DSS}, $V_{GS} = 0V$	-	-	25	μA
		V_{DS} = 0.8 x Rated BV_{DSS}, $V_{GS} = 0V$, $T_J = 125^oC$	-	-	250	μA
On-State Drain Current (Note 2)	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}$, $V_{GS} = 10V$ (Figure 7)	3.5	-	-	A
Gate to Source Leakage Forward	I_{GSS}	$V_{GS} = \pm 20V$	-	-	±100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$V_{GS} = 10V$, $I_D = 2.0A$ (Figures 8, 9)	-	0.8	1.000	Ω
Forward Transconductance (Note 2)	g_{fs}	$V_{DS} = 10V$, $I_D = 3.3A$ (Figure 12)	2.9	3.5	-	S
Turn-On Delay Time	$t_{d(ON)}$	$I_D \approx 3.5A$, $R_G = 9.1\Omega$, $V_{GS} = 10V$, $R_L = 49\Omega$ $V_{DD} = 175V$ (Figures 17, 18) MOSFET Switching Times are Essentially Independent of Operating Temperature	-	-	30	ns
Rise Time	t_r		-	-	35	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	-	55	ns
Fall Time	t_f		-	-	35	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_{g(TOT)}$	$V_{GS} = 10V$, $I_D = 3.5A$, $I_{G(REF)} = 1.5mA$, $V_{DS} = 0.8V$ x Rated BV_{DSS} (Figures 14, 19, 20) Gate Charge is Essentially Independent of Operating Temperature	-	18	30	nC
Gate to Source Charge	Q_{gs}		-	11	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	7.0	-	nC
Input Capacitance	C_{ISS}	$V_{GS} = 0V$, $V_{DS} = 25V$, f = 1.0MHz (Figure 11)	-	700	-	pF
Output Capacitance	C_{OSS}		-	150	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	40	-	pF
Internal Drain Inductance	L_D	Measured from the Drain Lead, 5mm (0.2in) from header to Center of Die / Modified MOSFET Symbol Showing the Internal Device Inductances	-	5.0	-	nH
Internal Source Inductance	L_S	Measured from the Source Lead, 5mm (0.2in) from Header to Source Bonding Pad 	-	15	-	nH
Junction to Case	$R_{\theta JC}$		-	-	5.0	^{o}C/W
Junction to Ambient	$R_{\theta JA}$	Free Air Operation	-	-	175	^{o}C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Rectifier. 	-	-	3.5	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	14	A
Source to Drain Diode Voltage (Note 2)	V_{SD}	$T_J = 25^oC$, $I_{SD} = 3.5A$, $V_{GS} = 0V$ (Figure 13)	-	-	1.6	V
Reverse Recovery Time	t_{rr}	$T_J = 150^oC$, $I_{SD} = 3.5A$, $dI_{SD}/dt = 100A/\mu s$	-	600	-	ns
Reverse Recovered Charge	Q_{RR}	$T_J = 150^oC$, $I_{SD} = 3.5A$, $dI_{SD}/dt = 100A/\mu s$	-	4.0	-	μC

NOTES:

2. Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%.
3. Repetitive Rating: pulse width limited by Max junction temperature. See Transient Thermal Impedance curve (Figure 3).
4. $V_{DD} = 50V$, start $T_J = 25^oC$, L = 42.85mH, $R_G = 25\Omega$, peak $I_{AS} = 3.5A$ (Figures 14,15).

Typical Performance Curves Unless Otherwise Specified

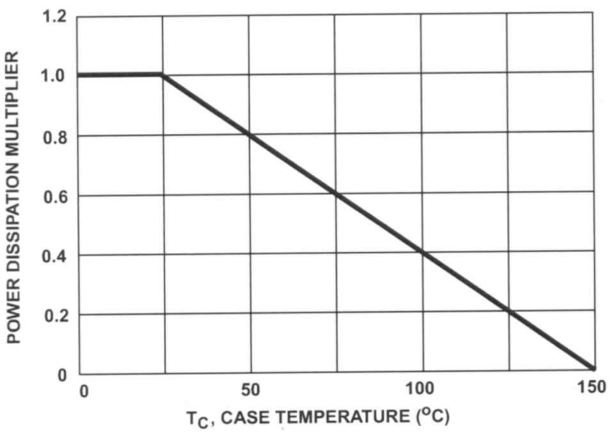


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

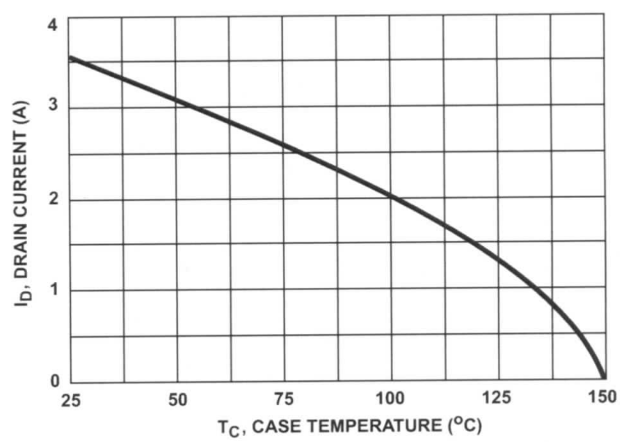


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

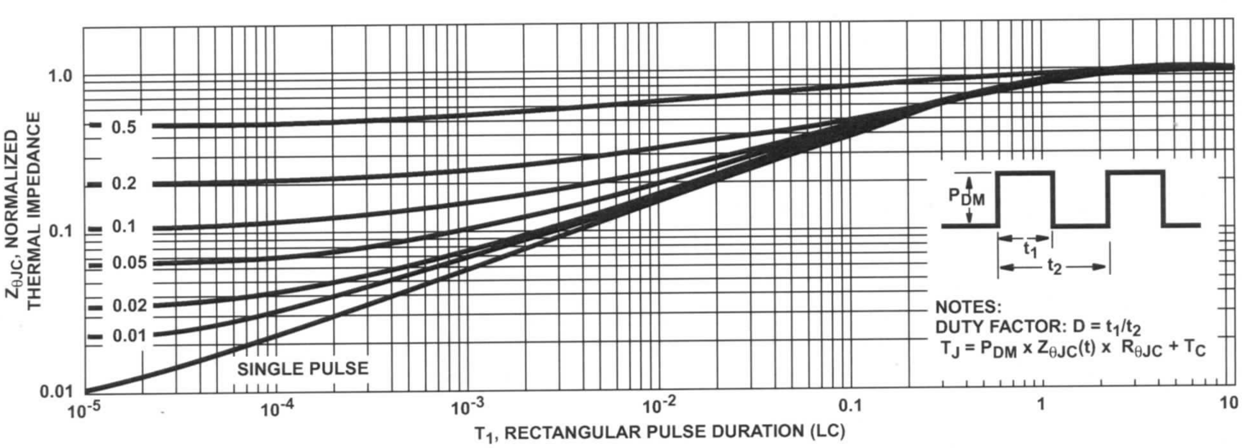


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE